

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

30C02CH – NPN Epitaxial Planar Silicon Transistor Low-Frequency General-Purpose Amplifier Applications

Applications

· Low-frequency Amplifier, high-speed switching, small motor drive

Features

- Large current capacity
- Low collector-to-emitter saturation voltage (resistance) $R_{CE}(sat)$ typ.=330m $\Omega[I_C=0.7A, I_B=35mA]$
- · Ultrasmall package facilitates miniaturization in end products
- Small ON-resistance (Ron)

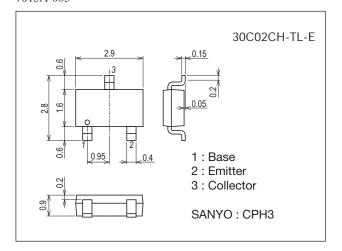
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO		30	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		700	mA
Collector Current (Pulse)	ICP		1.4	А
Collector Dissipation	PC	Mounted on a ceramic board (600mm ² ×0.8mm)	700	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7015A-003

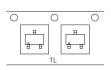


Product & Package Information

- Package
- : CPH3
- JEITA, JEDEC
- : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

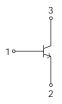
Packing Type: TL







Electrical Connection

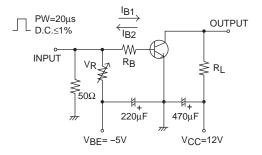


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Electrical Characteristics at Ta=25°C

Parameter Collector Cutoff Current Emitter Cutoff Current DC Current Gain Gain-Bandwidth Product Output Capacitance Collector-to-Emitter Saturation Voltage Base-to-Emitter Saturation Voltage	Symbol	Conditions		Unit			
Parameter	Symbol Conditions		min	typ	max		
Collector Cutoff Current	ICBO	VCB=30V, IE=0A			100	nA	
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			100	nA	
DC Current Gain	hFE	V _{CE} =2V, I _C =50mA	300		800		
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA		540		MHz	
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		3.3		pF	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =200mA, I _B =10mA		85	190	mV	
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =200mA, I _B =10mA		0.9	1.2	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μΑ, I _E =0Α	40			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	30			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μΑ, IC=0A	5			V	
Turn-On Time	ton			35		ns	
Storage Time	tstg	See specified Test Circuit.		255		ns	
Fall Time	tf			40		ns	

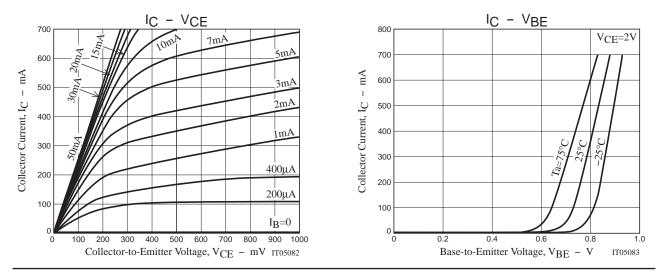
Switching Time Test Circuit



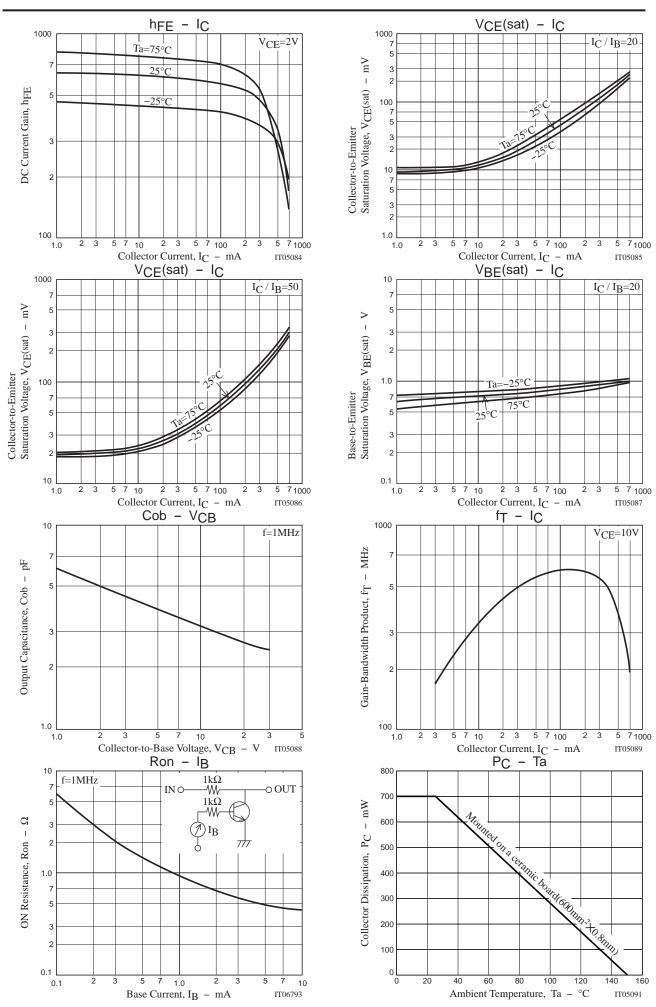
IC=20IB1=-20IB2=300mA

Ordering Information

5					
Device	Device Package		memo		
30C02CH-TL-E	CPH3	3,000pcs./reel	Pb Free		



30C02CH



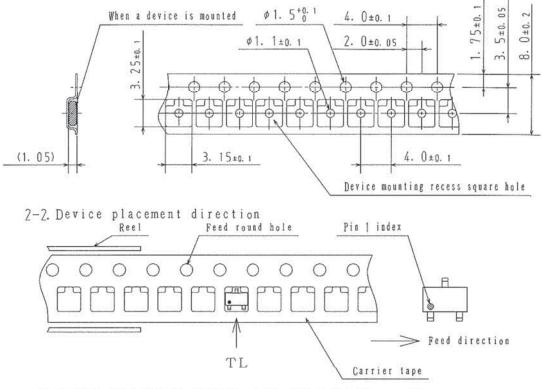
Embossed Taping Specification 30C02CH-TL-E

1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)		Packing format						
14-501-50-	Type	Reel Inner box Outer box		Inner BOX (C-1)			Outer BOX (A-7)			
СРНЗ	CPH3 3.000		3, 000 15, 000 90, 000		5 reels contained Dimensions:mm (external)			6 inner boxes contained) Dimensions:mm (external)		
					The second second	×72×		A STATE OF A		
Packing met	:hod		Reel	(u 1	nit:mr	<u>x label</u>)	It i The	<u>ter box label</u> is a label at the time of factory shipme form of a label may change in physical tribution process.		
	Type				t INDE A THE A CONTRACTOR OF A CONTRACT OF A			108 TYPE CODE •000000000000000000000000000000000000		
	Quan	tity		CTY 0, 00 111111 1111 11111 SPECIAL # 11111 11111 # 20 7 2 2 (SSEMELY: ****	0 ⁽¹⁾ LEAD	+ +	8 0	GTY O, 000 PCS LEAD FREE # LOT OCCONTRACTOR OF CONTRACTOR		
	Reel la		NOTE	: (1) e LBAD FI	REE 💥 de	scription		special #20722005310C* ASSEMBLY:**** (DIFFUSICN:****) that the surface		
	Version and the second second	147 - 148 A	tr -	eatment o						
				Label LEAD FRE	Company of the second second	JEITA JEITA P	Phase 3			
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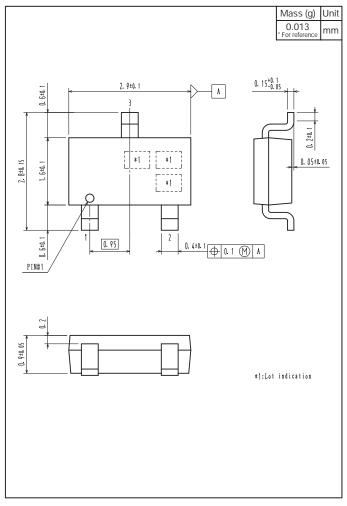
2. Taping configuration

2-1. Carrier tape size (unit:mm)

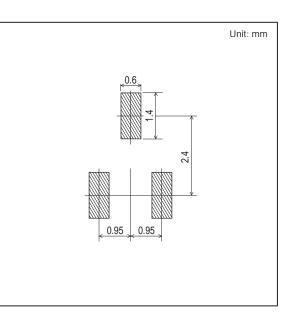


Those with one electrode terminal on the feed hole side ·····TL

Outline Drawing 30C02CH-TL-E



Land Pattern Example



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